

21	15967	((356/399,400,401,388,614).CCLS.) ((250/492.2,491.1,548,559.29,559.3,559.36). ((355/53,55,67,77).CCLS.) ((430/22,30,5).CCLS.) ((382/151).CCLS.)	USPAT; US-PGPUB	2004/04/29 11:19
22	3717	((438/401).CCLS.) ((382/151).CCLS.) ((250/492.2,491.1,548,559.29,559.3,559.36). ((355/53,55,67,77).CCLS.) ((430/22,30,5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same (photomask mask reticle) same (wafer semiconduct\$ substrate))) and ((mask photomask reticle) same phase) same ("0" "180" pi)) same align\$)) and ((align\$ near (mark\$ pattern\$ target\$ grat\$3)) near (mark\$ pattern\$ target\$ grat\$3))	USPAT; US-PGPUB	2004/04/29 11:19
23	1026	((438/401).CCLS.) ((382/151).CCLS.) ((250/492.2,491.1,548,559.29,559.3,559.36). ((355/53,55,67,77).CCLS.) ((430/22,30,5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same (photomask mask reticle) same (wafer semiconduct\$ substrate))) and ((mask photomask reticle) same phase) same ("0" "180" pi)) same align\$)) and ((align\$ near (mark\$ pattern\$ target\$ grat\$3)) near (mark\$ pattern\$ target\$ grat\$3))	USPAT; US-PGPUB	2004/04/29 11:20
24	308	((438/401).CCLS.) ((382/151).CCLS.) ((250/492.2,491.1,548,559.29,559.3,559.36). ((355/53,55,67,77).CCLS.) ((430/22,30,5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same (photomask mask reticle) same (wafer semiconduct\$ substrate))) and ((mask photomask reticle) same phase) same ("0" "180" pi)) same align\$)) and ((align\$ near (mark\$ pattern\$ target\$ grat\$3)) near (mark\$ pattern\$ target\$ grat\$3))	USPAT; US-PGPUB	2004/04/29 11:27
25	80	((438/401).CCLS.) ((382/151).CCLS.) ((250/492.2,491.1,548,559.29,559.3,559.36). ((355/53,55,67,77).CCLS.) ((430/22,30,5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same (photomask mask reticle) same (wafer semiconduct\$ substrate))) and ((mask photomask reticle) same phase) same ("0" "180" pi)) same align\$)) and ((align\$ near (mark\$ pattern\$ target\$ grat\$3)) near (mark\$ pattern\$ target\$ grat\$3))	USPAT; US-PGPUB	2004/04/29 11:33
26	45	((438/401).CCLS.) ((382/151).CCLS.) ((250/492.2,491.1,548,559.29,559.3,559.36). ((355/53,55,67,77).CCLS.) ((430/22,30,5).CCLS.) ((382/151).CCLS.) ((438/401).CCLS.)) and (align\$ same (photomask mask reticle) same (wafer semiconduct\$ substrate))) and ((mask photomask reticle) same phase) same ("0" "180" pi)) same align\$)) and ((align\$ near (mark\$ pattern\$ target\$ grat\$3)) near (mark\$ pattern\$ target\$ grat\$3))	USPAT; US-PGPUB	2004/04/29 12:26
27	16	carpi.in.	USPAT	2004/04/29 11:58
29	34	carpi.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT	2004/04/29 12:30
30	1	2003-755598.NRAN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT	2004/04/29 12:28
31	87	liegl.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT	2004/04/29 12:32
32	2	(bernhard and liegl).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT	2004/04/29 12:30
33	17	thwaite.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB DERWENT	2004/04/29 12:32